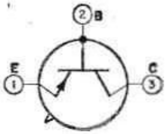
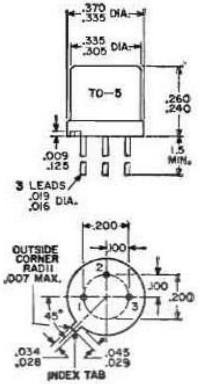
TRANSISTOR

2N396
2N396A

Germanium p-n-p types used in medium-speed switching applications in data-processing equipment. JEDEC No. TO-5 package; outline 6, Outlines Section. Ratings for these types are the same as for type 2N395 except for the following items:





MAXIMUM RATINGS

	2N396	*2N396A*	
Collector-to-Emitter Voltage:			
With base open	—	—20 max	volts
With external base-to-emitter resistance = 10000 ohms	—20 max	—	volts
Transistor Dissipation:			
At ambient temperatures up to 25°C	150 max	200 max	mw

CHARACTERISTICS

Collector-to-Emitter Saturation Voltage (with collector ma = —50 and base ma = —3.3)	—0.2 max	volt
Collector-Cutoff Current (with collector-to-base volts = —20 and emitter current = 0)	—6 max	μa
In Common-Base Circuit		
Collector-to-Base Capacitance (with collector-to-base volts = —5 and emitter ma = 1)	20 max	pf
Forward-Current-Transfer-Ratio Cutoff Frequency (with collector-to-base volts = —5 and emitter ma = 1)	5 min	Mc
In Common-Emitter Circuit		
DC Forward Current-Transfer Ratio:		
With collector-to-emitter volts = —1 and collector ma = —10	30 to 150	
With collector-to-emitter volts = —0.35 and collector ma = —200	15 min	